

NPN general purpose double transistor

PUMX1

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 40 V)
- Reduces number of components and boardspace.

APPLICATIONS

- General purpose switching and amplification.

DESCRIPTION

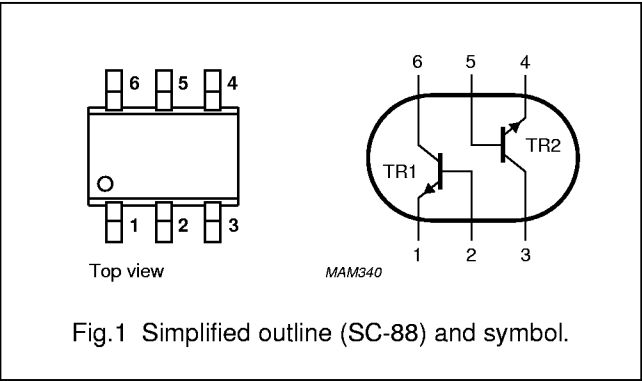
Two independently operating NPN transistors in an SC-88 plastic package. PNP complement: PUMT1.

MARKING

TYPE NUMBER	MARKING CODE
PUMX1	ZtZ

PINNING

PIN	DESCRIPTION
1, 4	emitter TR1; TR2
2, 5	base TR1; TR2
3, 6	collector TR2; TR1



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transistor					
V_{CBO}	collector-base voltage	open emitter	—	50	V
V_{CEO}	collector-emitter voltage	open base	—	40	V
V_{EBO}	emitter-base voltage	open collector	—	5	V
I_C	collector current (DC)		—	100	mA
I_{CM}	peak collector current		—	200	mA
I_{BM}	peak base current		—	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	—	200	mW
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		—	150	°C
T_{amb}	operating ambient temperature		−65	+150	°C
Per device					
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	—	300	mW

Note

1. Device mounted on an FR4 printed-circuit board.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per device				
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	416	K/W

Note

1. Device mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transistor					
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 30\text{ V}$	–	100	nA
		$I_E = 0; V_{CB} = 30\text{ V}; T_J = 150\text{ °C}$	–	10	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 4\text{ V}$	–	100	nA
h_{FE}	DC current gain	$I_C = 1\text{ mA}; V_{CE} = 6\text{ V}$	120	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 50\text{ mA}; I_B = 5\text{ mA}; \text{note 1}$	–	200	mV
C_c	collector capacitance	$I_E = I_e = 0; V_{CB} = 12\text{ V}; f = 1\text{ MHz}$	–	1.5	pF
f_T	transition frequency	$I_C = 2\text{ mA}; V_{CE} = 12\text{ V}; f = 100\text{ MHz}$	100	–	MHz

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT363

